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# 2SA1190, 2SA1191

Silicon PNP Epitaxial

# HITACHI

ADE-208-1012 (Z)  
1st. Edition  
Mar. 2001

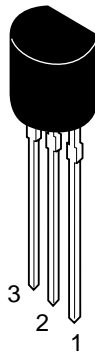
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## Application

- Low frequency low noise amplifier
- Complementary pair with 2SC2855 and 2SC2856

## Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

2SA1190, 2SA1191

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	2SA1190	2SA1191	Unit
Collector to base voltage	V <sub>CBO</sub>	−90	−120	V
Collector to emitter voltage	V <sub>CEO</sub>	−90	−120	V
Emitter to base voltage	V <sub>EBO</sub>	−5	−5	V
Collector current	I <sub>C</sub>	−100	−100	mA
Emitter current	I <sub>E</sub>	100	100	mA
Collector power dissipation	P <sub>C</sub>	400	400	mW
Junction temperature	T <sub>j</sub>	150	150	°C
Storage temperature	T <sub>stg</sub>	−55 to +150	−55 to +150	°C

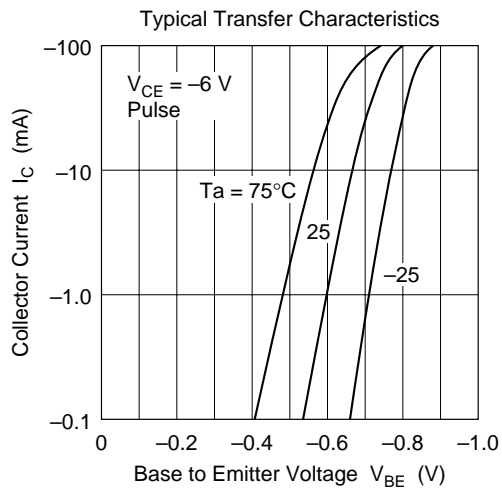
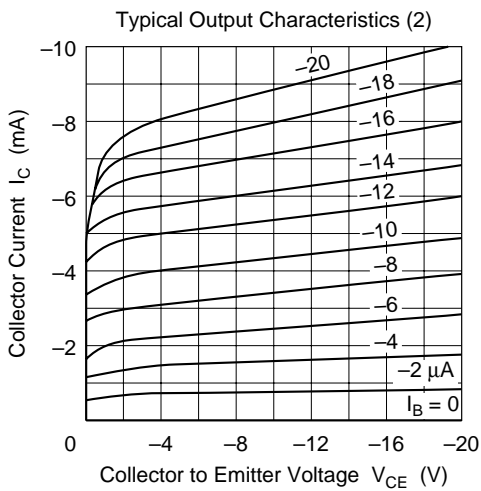
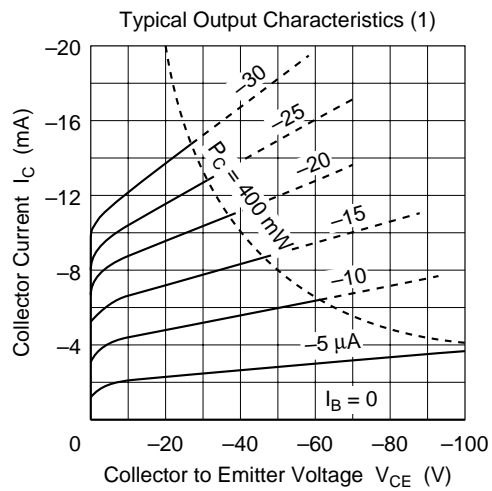
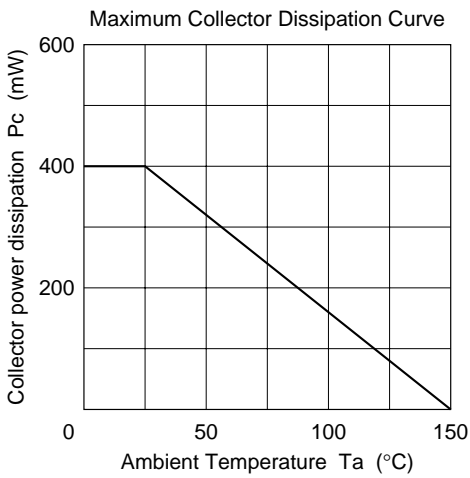
## Electrical Characteristics (Ta = 25°C)

Item	Symbol	2SA1190			2SA1191			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	-90	—	—	-120	—	—	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-90	—	—	-120	—	—	V	$I_C = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	-5	—	—	V	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	-0.1	—	—	-0.1	$\mu A$	$V_{CB} = -70 \text{ V}, I_E = 0$
Emitter cutoff current	$I_{EBO}$	—	—	-0.1	—	—	-0.1	$\mu A$	$V_{EB} = -2 \text{ V}, I_C = 0$
DC current transfer ratio	$h_{FE}^{*1}$	250	—	800	250	—	800		$V_{CE} = -12 \text{ V},$ $I_C = -2 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	-0.05	-0.15	—	-0.05	-0.15	V	$I_C = -10 \text{ mA},$ $I_B = -1 \text{ mA}^{*2}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	-0.7	-1.0	—	-0.7	-1.0	V	
Gain bandwidth product	$f_T$	—	130	—	—	130	—	MHz	$V_{CE} = -6 \text{ V},$ $I_C = -10 \text{ mA}$
Collector output capacitance	$C_{ob}$	—	3.2	—	—	3.2	—	pF	$V_{CB} = -10 \text{ V}, I_E = 0,$ $f = 1 \text{ MHz}$
Noise figure	NF	—	0.15	1.5	—	0.15	1.5	dB	$V_{CE} = -6 \text{ V},$ $I_C = -0.1 \text{ mA},$ $R_g = 10 \text{ k}\Omega$ $f = 1 \text{ kHz}$
		—	0.2	2.0	—	0.2	2.0	dB	$V_{CE} = -6 \text{ V},$ $I_C = -0.1 \text{ mA},$ $R_g = 10 \text{ k}\Omega$ $f = 10 \text{ Hz}$
Noise voltage referred to input	$e_n$	—	0.7	—	—	0.7	—	nV/ $\sqrt{\text{Hz}}$	$V_{CB} = -6 \text{ V},$ $I_C = -10 \text{ mA},$ $R_g = 0, f = 1 \text{ kHz}$

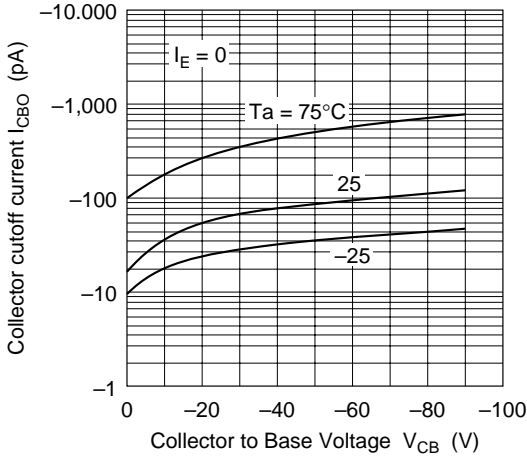
Notes: 1. The 2SA1190 and 2SA1191 are grouped by  $h_{FE}$  as follows.

2. Pulse test

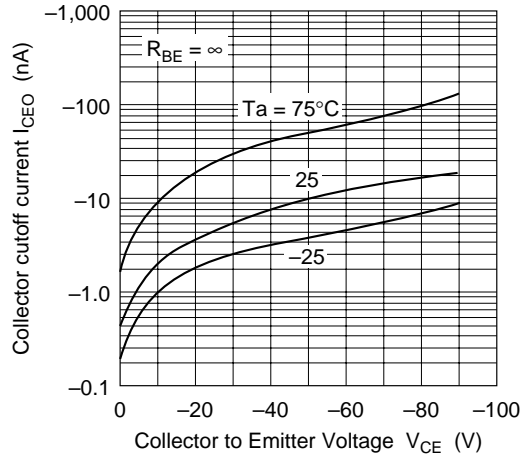
D	E
250 to 500	400 to 800



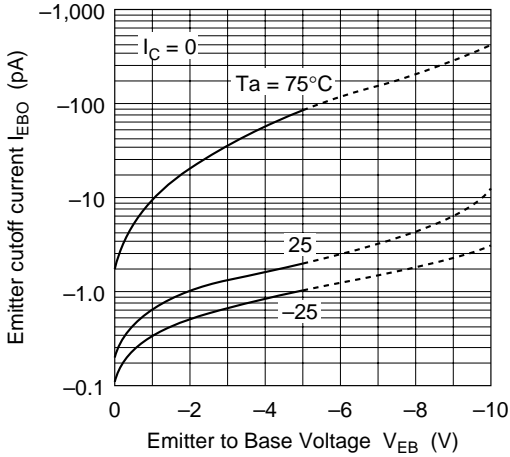
Collector Cutoff Current vs.  
Collector to Base Voltage



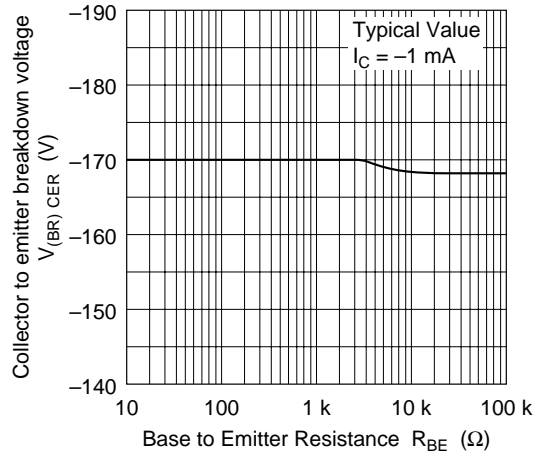
Collector Cutoff Current vs.  
Collector to Emitter Voltage



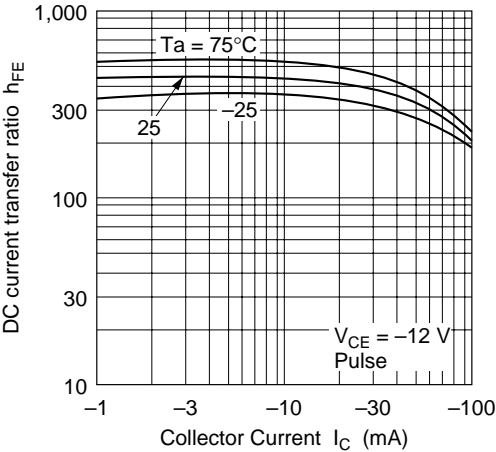
Emitter Cutoff Current vs.  
Emitter to Base Voltage



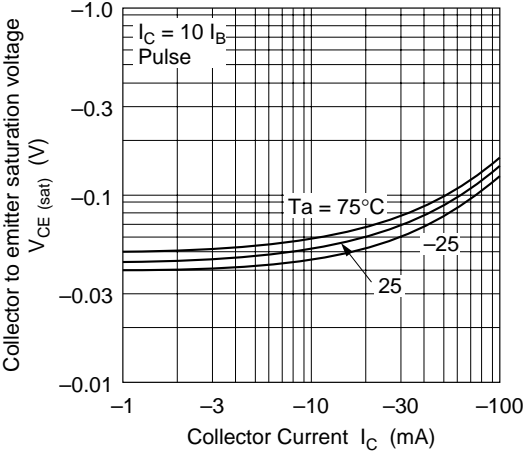
Collector to Emitter Breakdown Voltage vs.  
Base to Emitter Resistance



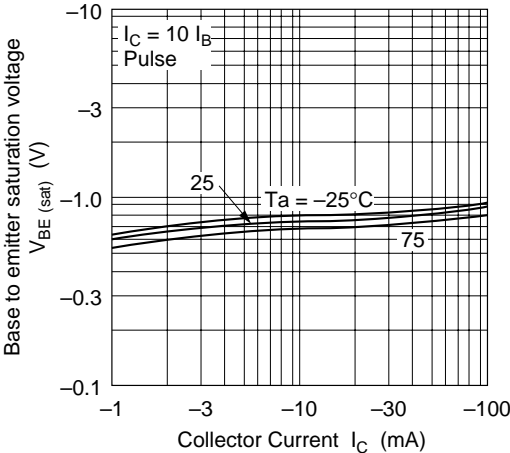
DC Current Transfer Ratio vs.  
Collector Current



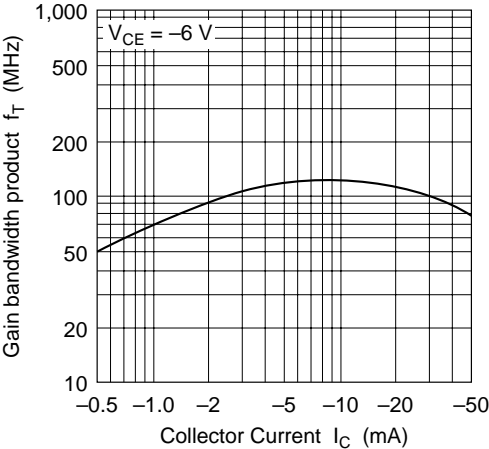
Collector to Emitter Saturation Voltage vs.  
Collector Current

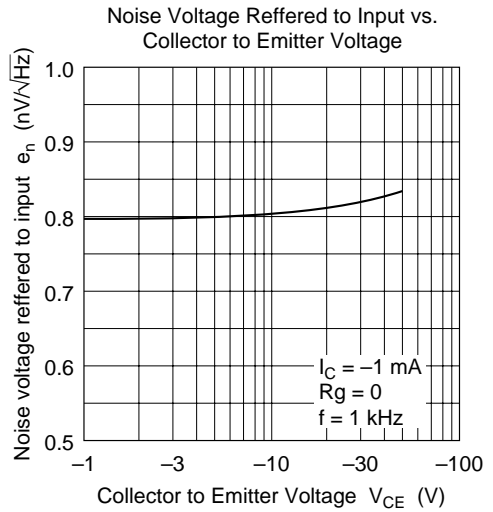
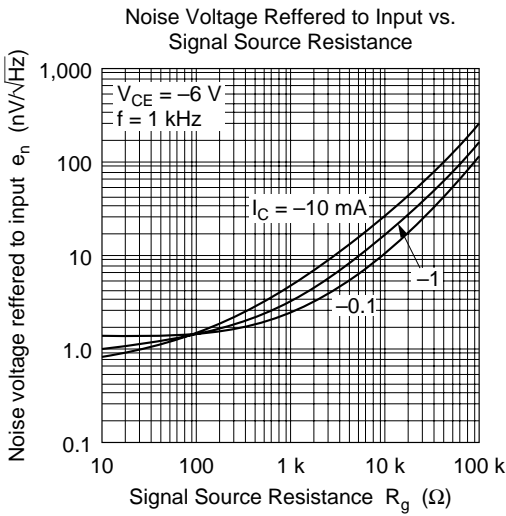
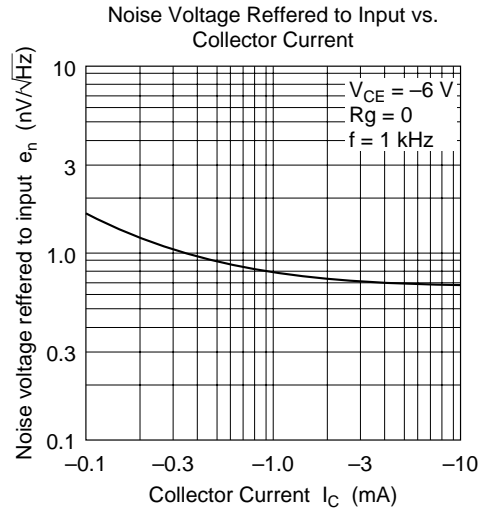
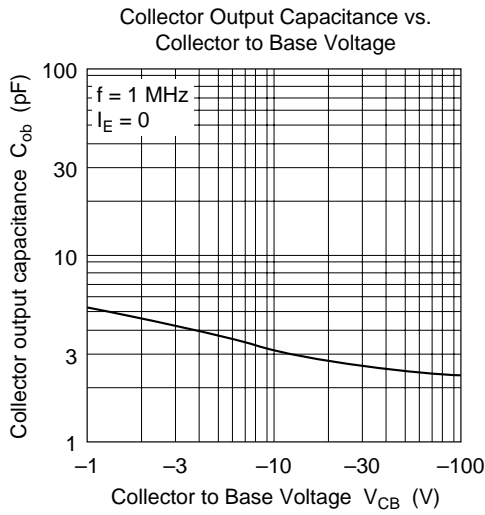


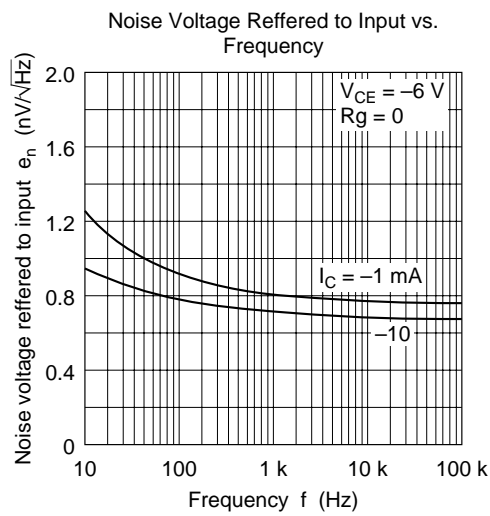
Base to Emitter Saturation Voltage vs.  
Collector Current



Gain Bandwidth Product vs.  
Collector Current





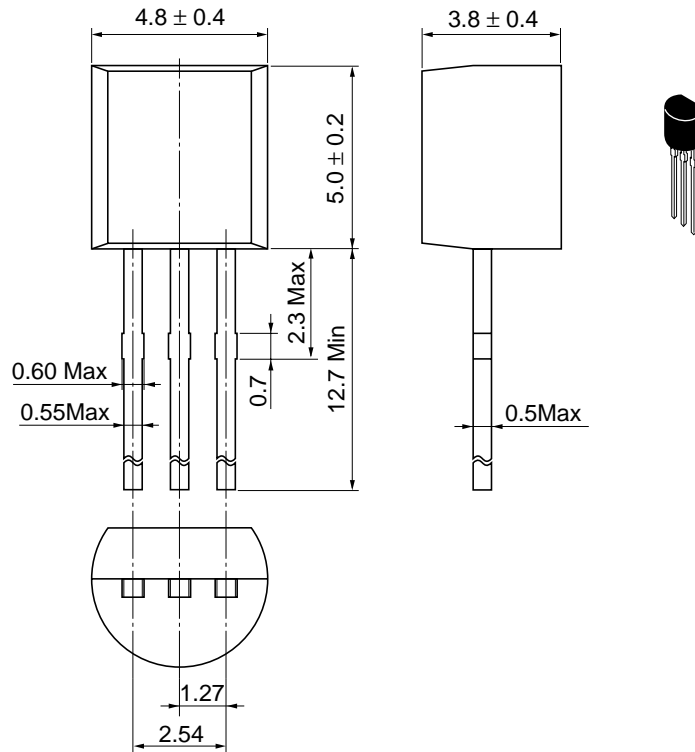




# Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	0.25 g

## Cautions

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# HITACHI

## Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	: <a href="http://semiconductor.hitachi.com/">http://semiconductor.hitachi.com/</a>
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### For further information write to:

Hitachi Semiconductor  
(America) Inc.  
179 East Tasman Drive,  
San Jose, CA 95134  
Tel: <1> (408) 433-1990  
Fax: <1> (408) 433-0223

Hitachi Europe GmbH  
Electronic Components Group  
Dornacher Straße 3  
D-85622 Feldkirchen, Munich  
Germany  
Tel: <49> (89) 9 9180-0  
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.  
Electronic Components Group.  
Whitebrook Park  
Lower Cookham Road  
Maidenhead  
Berkshire SL6 8YA, United Kingdom  
Tel: <44> (1628) 585000  
Fax: <44> (1628) 585160

Hitachi Asia Ltd.  
Hitachi Tower  
16 Collyer Quay #20-00,  
Singapore 049318  
Tel: <65>-538-6533/538-8577  
Fax: <65>-538-6933/538-3877  
URL: <http://www.hitachi.com.sg>

Hitachi Asia Ltd.  
(Taipei Branch Office)  
4/F, No. 167, Tun Hwa North Road,  
Hung-Kuo Building,  
Taipei (105), Taiwan  
Tel: <886>-(2)-2718-3666  
Fax: <886>-(2)-2718-8180  
Telex: 23222 HAS-TP  
URL: <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.  
Group III (Electronic Components)  
7/F., North Tower,  
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Tsim Sha Tsui, Kowloon,  
Hong Kong  
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